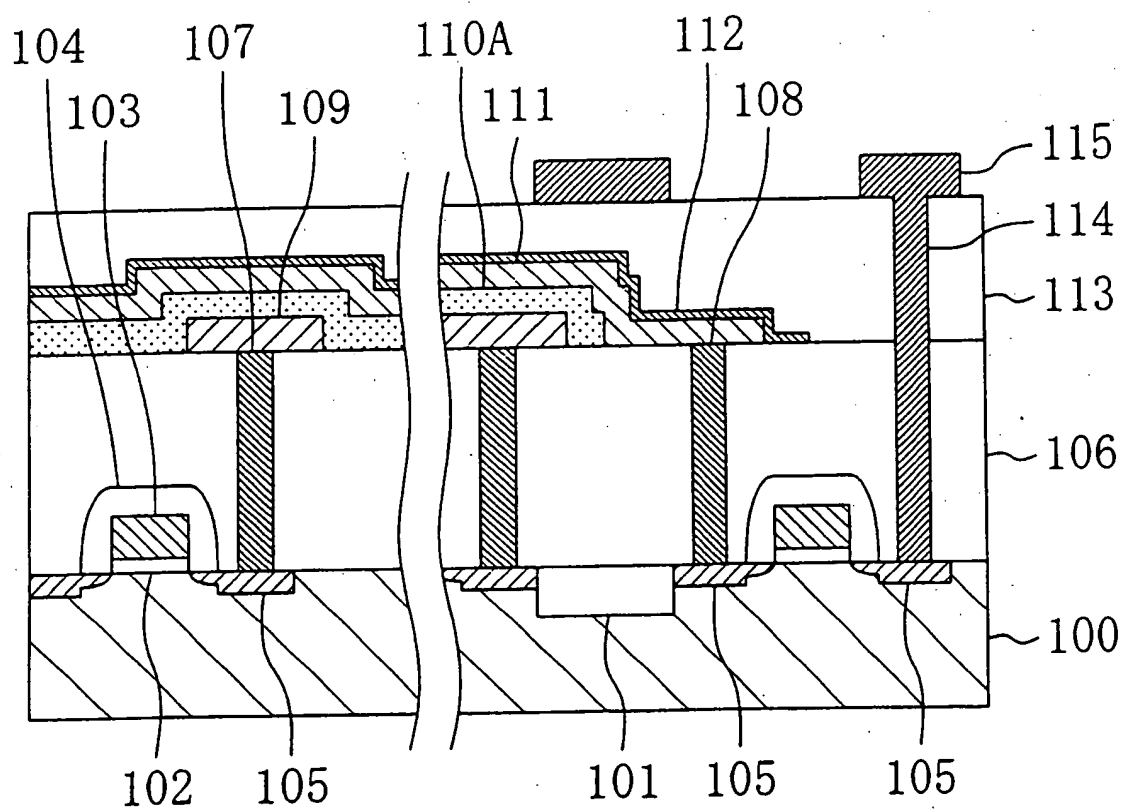


Fig. 1



This diagram shows a cross-sectional view of a semiconductor device, similar to the one in Figure 1, but with a central gap. The substrate 100 is divided into two symmetrical halves by a vertical gap. Each half contains a central rectangular region 101, a pair of side regions 102 and 103, and a pair of vertical regions 104 and 105. A top layer 106 is present, with a central opening 107 in each half. A bottom layer 108 is located beneath the central region 101 in each half. The device is symmetrical about a central vertical axis.

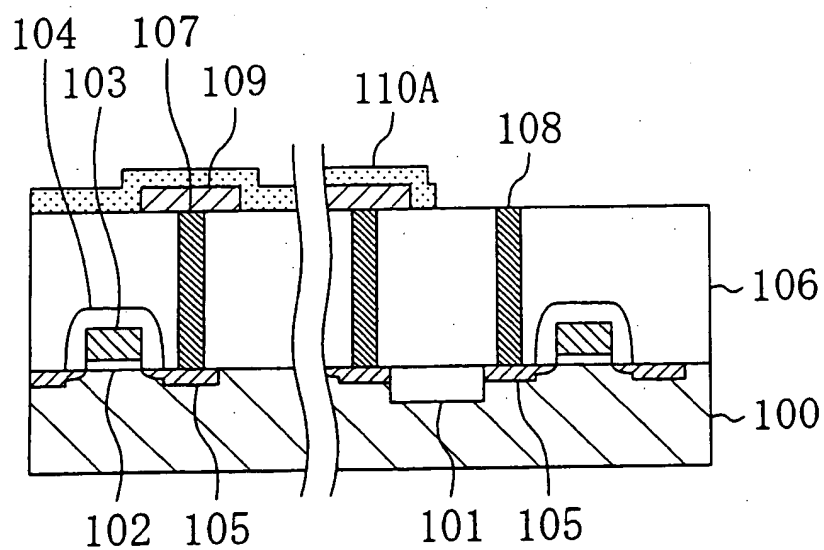


Fig. 2 (b)

Fig. 3(a)

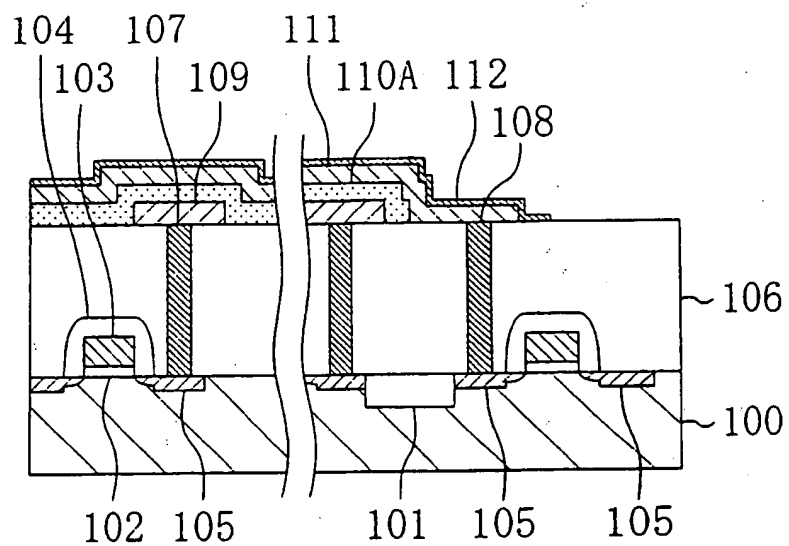


Fig. 3(b)

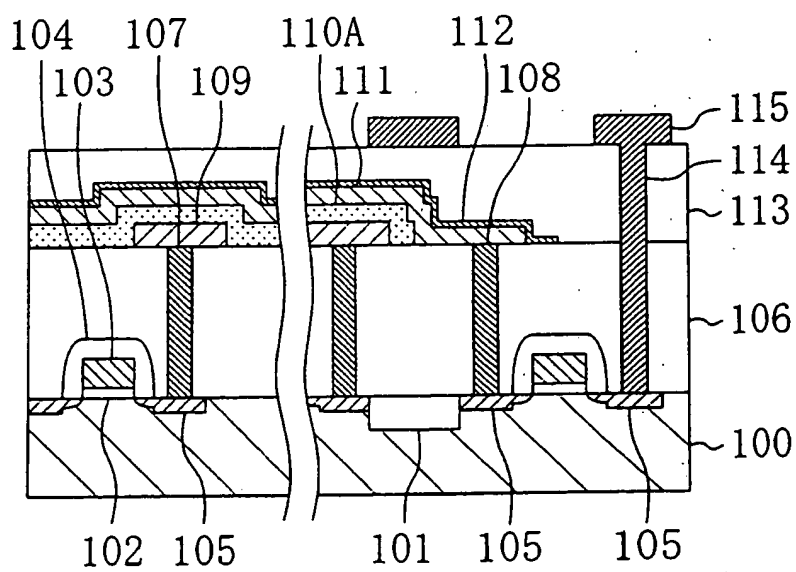


Fig. 4

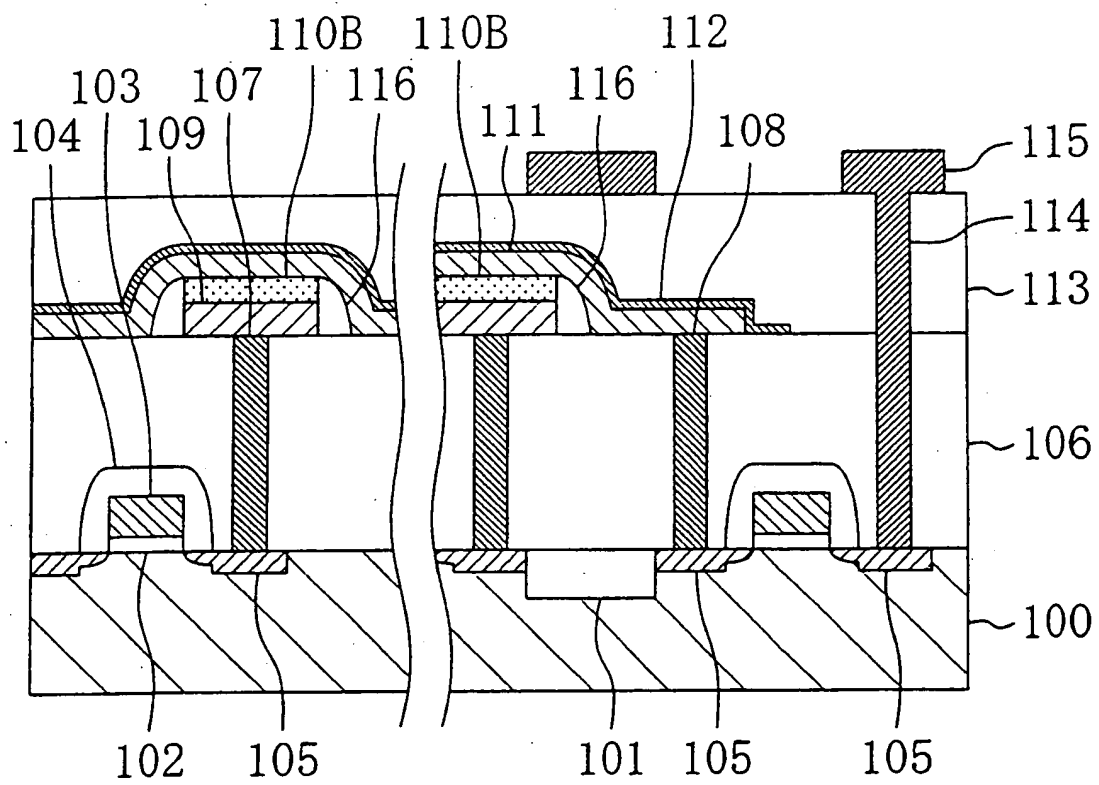


Fig. 5(a)

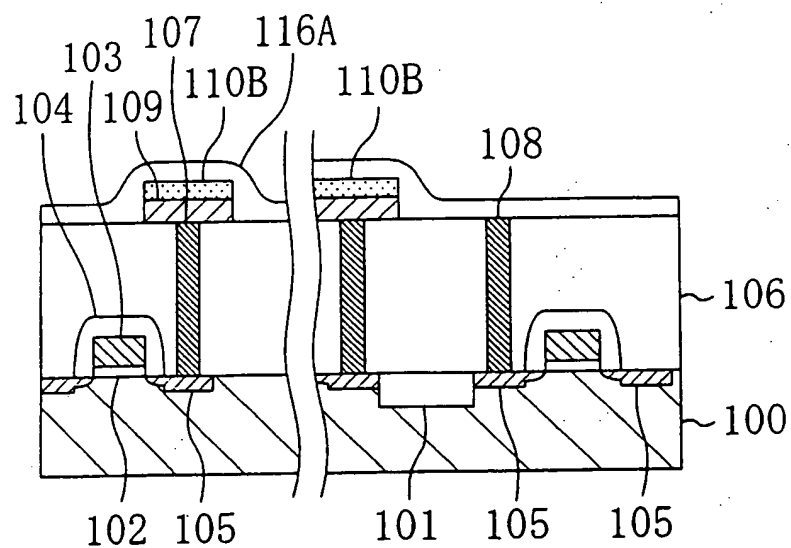


Fig. 5(b)

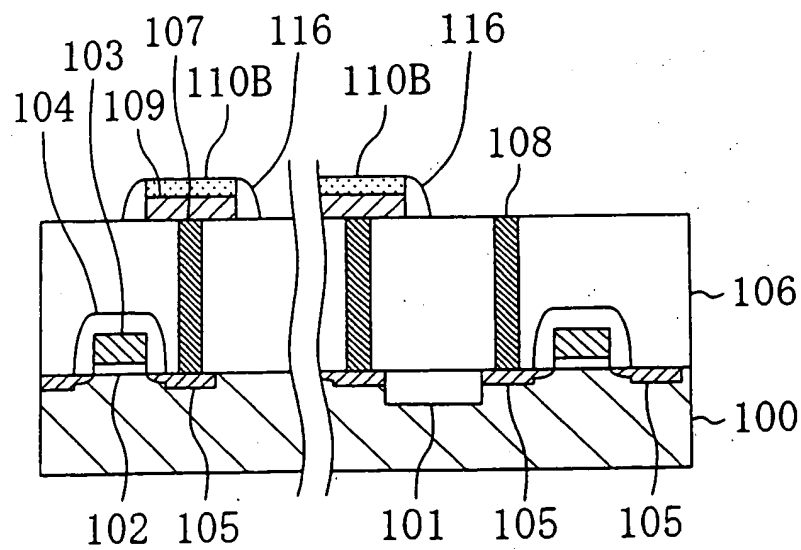


Fig. 6

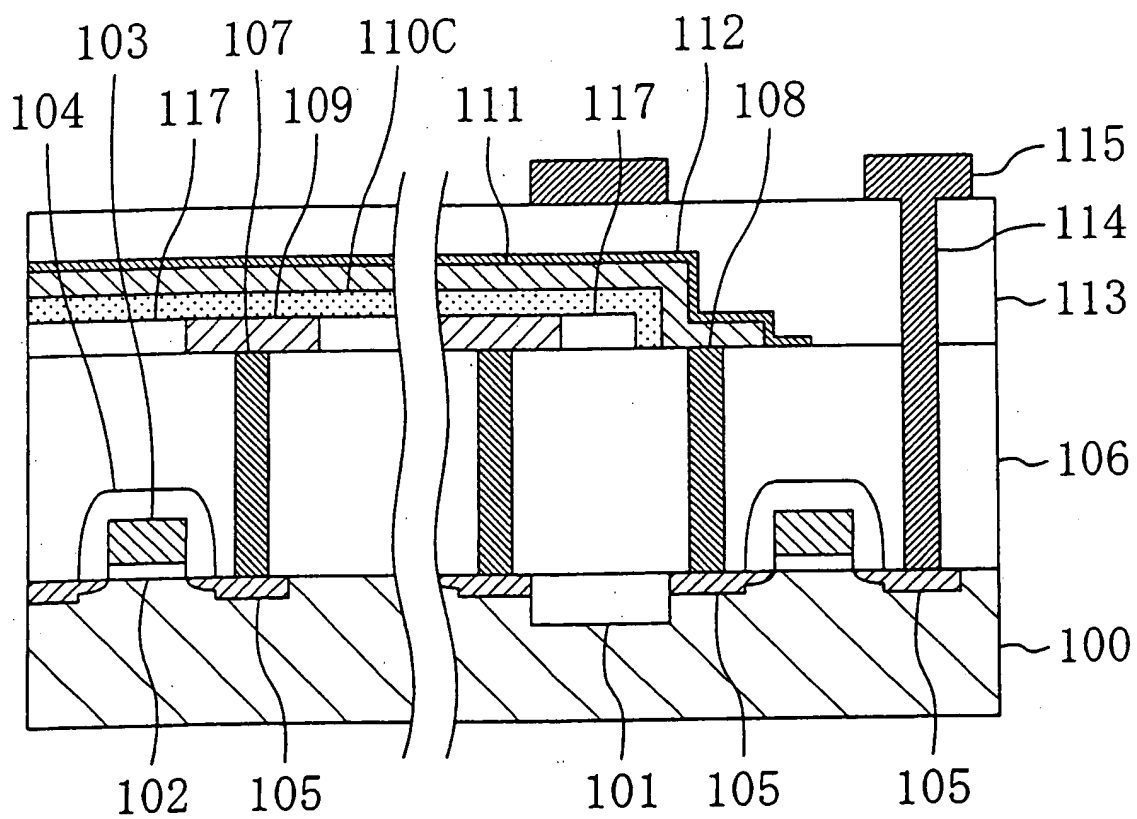


Fig. 7(a)

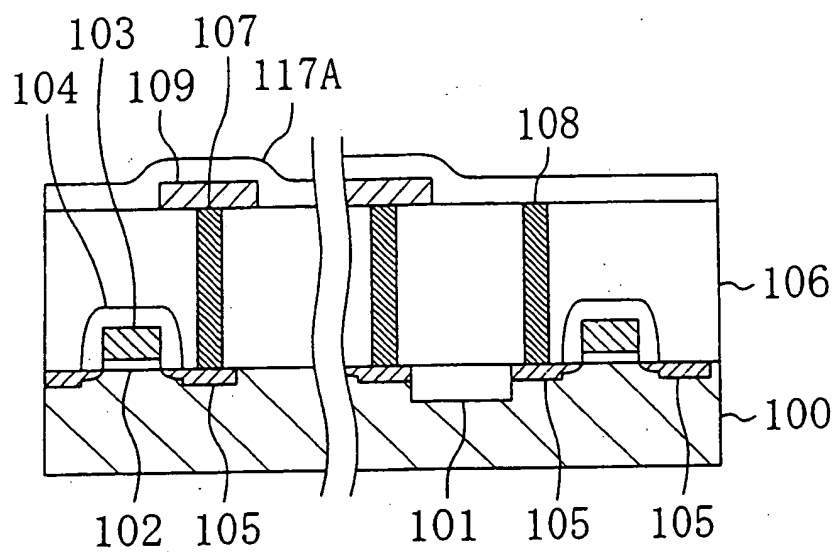
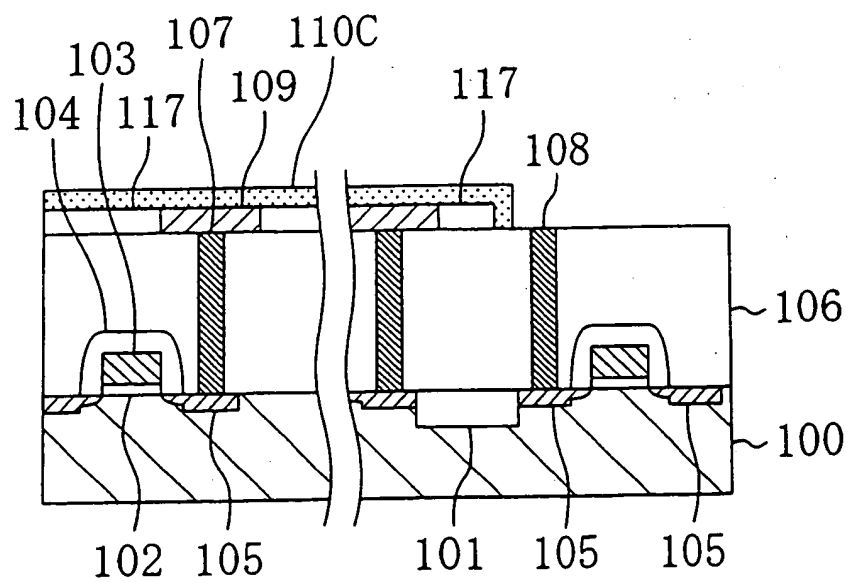


Fig. 7(b)



## Prior Art

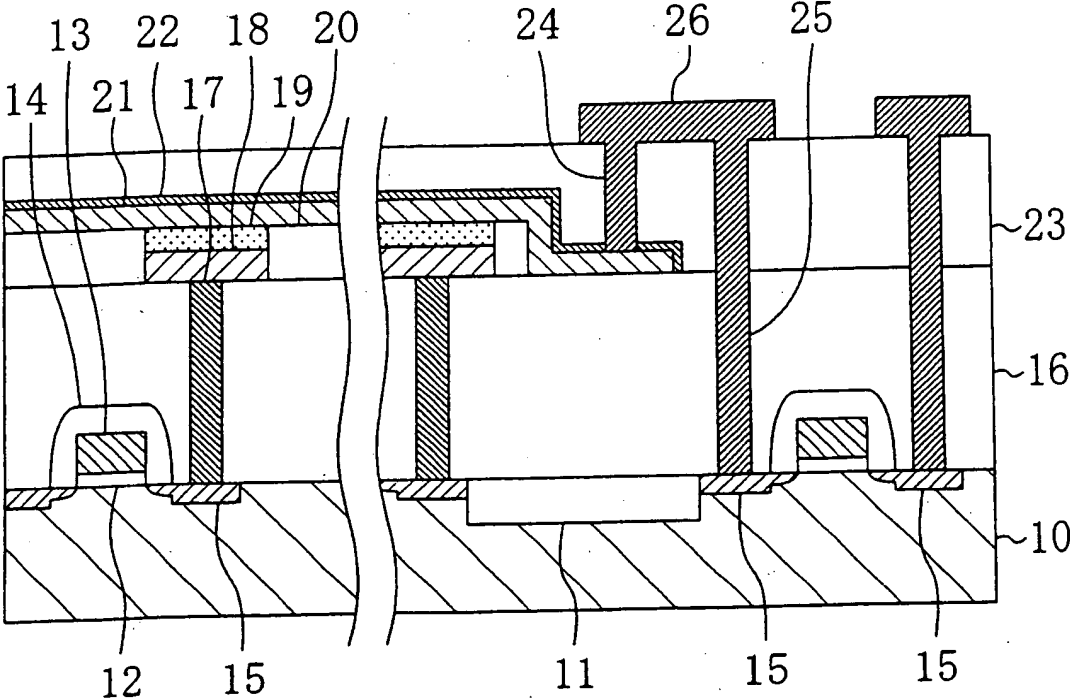




Fig. 9(a)  
Prior Art

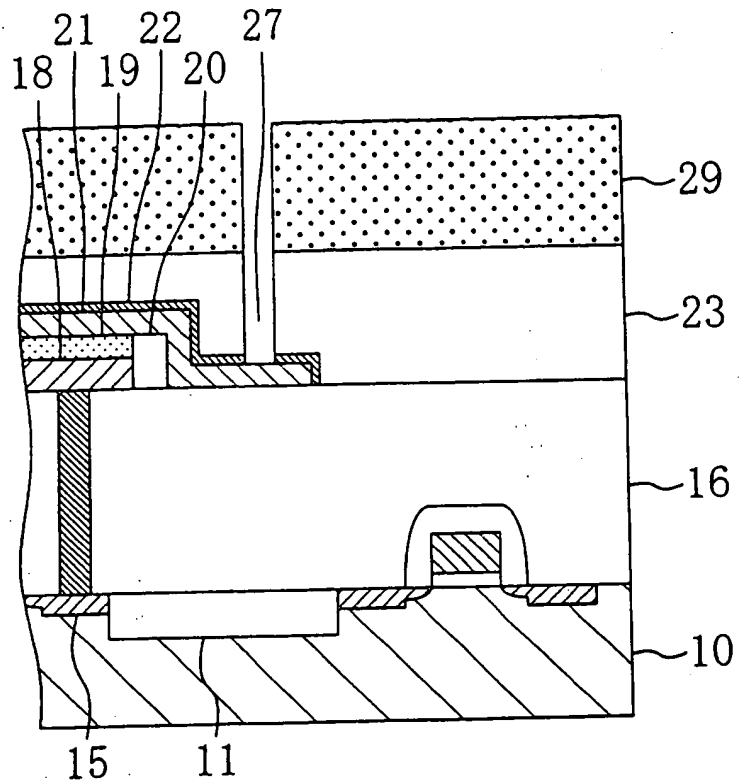


Fig. 9(b)  
Prior Art

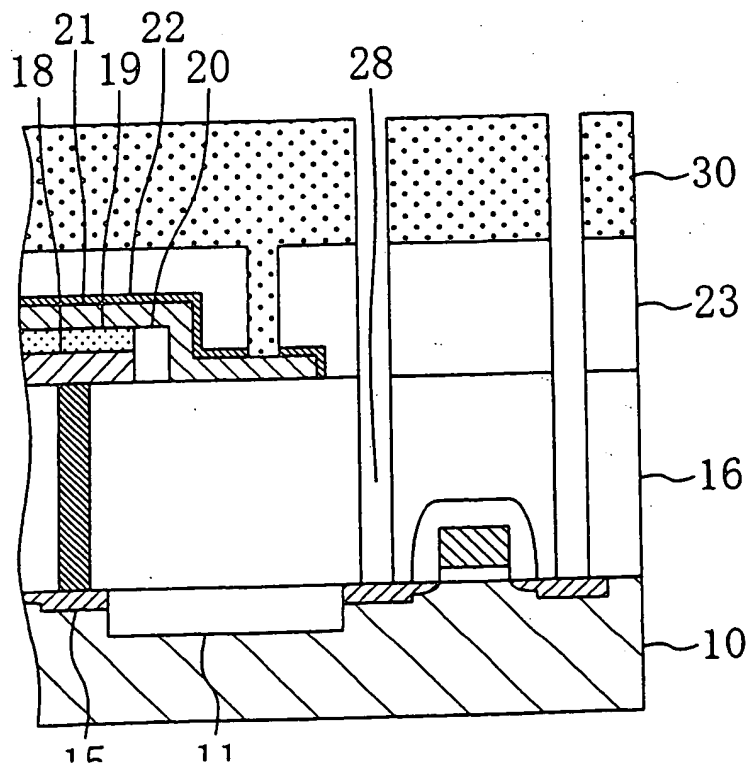


Fig. 10(a)  
Prior Art

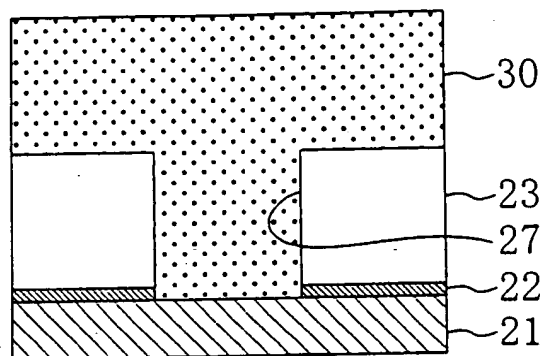


Fig. 10(b)  
Prior Art

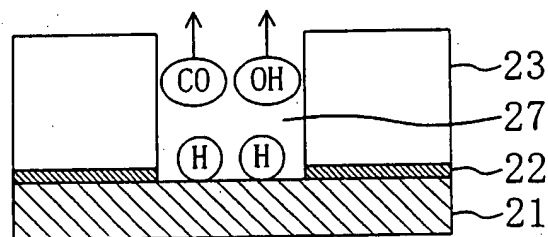


Fig. 10(c)  
Prior Art

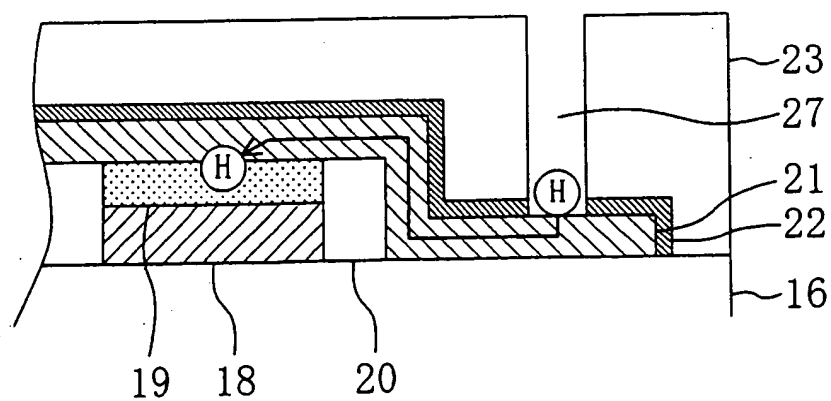


Fig. 11  
Prior Art

